

30V N-Channel Mosfet

**FEATURES**

TO-252-2L

RDS(ON)≤ 5m Ω @VGS=10V

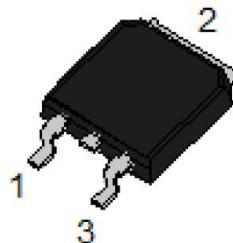
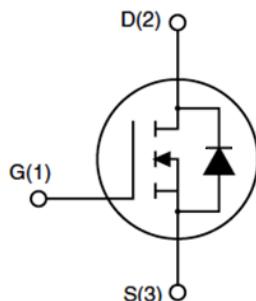
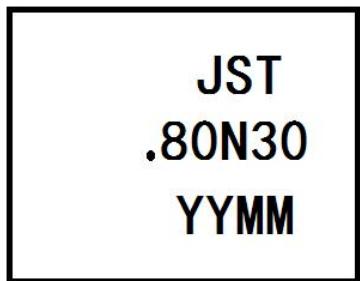
RDS(ON)≤ 7.5m Ω @VGS=4.5V

**APPLICATIONS**

Load Switch

PWM Application

Power Management

**MARKING****N-CHANNEL MOSFET**

YYMM:Date Code(year&amp;month)

**Absolute Maximum Ratings** ( $T_c=25^\circ\text{C}$  unless otherwise specified)

Symbol	Param		Max.	Units
$V_{DSS}$	Drain-Source Voltage		30	V
$V_{GSS}$	Gate-Source Voltage		$\pm 20$	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ\text{C}$	90	A
		$T_c = 100^\circ\text{C}$	58	A
$I_{DM}$	Pulsed Drain Current <sup>note1</sup>		360	A
$E_{AS}$	Single Pulsed Avalanche Energy <sup>note2</sup>		250	mJ
$P_D$	Power Dissipation	$T_c = 25^\circ\text{C}$	90	W
$R_{eJC}$	Thermal Resistance, Junction to Case		1.67	$^\circ\text{C}/\text{W}$
$T_J, T_{STG}$	Operating and Storage Temperature Range		-55 to +175	$^\circ\text{C}$

**Electrical Characteristics** ( $T_c=25^\circ\text{C}$  unless otherwise specified)

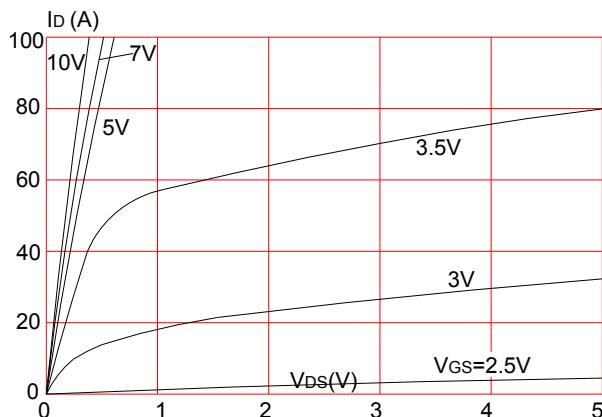
Symbol	Param	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	30	-	-	V
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{DS}=30\text{V}, V_{GS}=0\text{V}$ ,	-	-	1.0	$\mu\text{A}$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.0	1.5	2.5	V
$R_{DS(\text{on})}$	Static Drain-Source on-Resistance note3	$V_{GS}=10\text{V}, I_D=20\text{A}$	-	3.6	5	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=15\text{A}$	-	5	7.5	
$g_{FS}$	Forward Transconductance	$V_{DS}=5\text{V}, I_D=15\text{A}$	-	28	-	S
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=15\text{V}, V_{GS}=0\text{V}, f=1.0\text{MHz}$	-	1950	-	pF
$C_{oss}$	Output Capacitance		-	320	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	240	-	pF
$Q_g$	Total Gate Charge	$V_{DS}=25\text{V}, I_D=20\text{A}, V_{GS}=10\text{V}$	-	42	-	nC
$Q_{gs}$	Gate-Source Charge		-	4	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	14	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=15\text{V}, R_i=0.75\Omega, R_{GEN}=3\Omega, V_{GS}=10\text{V}$	-	13	-	ns
$t_r$	Turn-on Rise Time		-	36	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	43	-	ns
$t_f$	Turn-off Fall Time		-	16	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_s$	Maximum Continuous Drain to Source Diode Forward Current	-	-	90	-	A
$I_{sM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	-	360	-	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS}=0\text{V}, I_s=30\text{A}$	-	-	1.2	V
$trr$	Body Diode Reverse Recovery Time	$I_f=20\text{A}, dI/dt=100\text{A}/\mu\text{s}$	-	16	-	ns
$Qrr$	Body Diode Reverse Recovery Charge		-	5	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

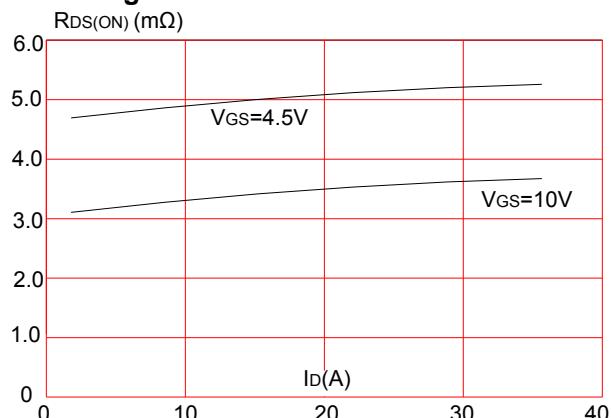
2. EAS condition  $T_J=25^\circ\text{C}, VDD=30\text{V}, VG=10\text{V}, L=0.5\text{mH}, RG=25\Omega$

## Typical Performance Characteristics

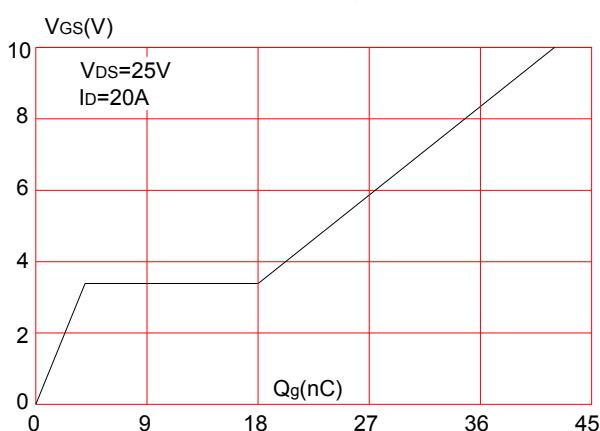
**Figure 1:** Output Characteristics



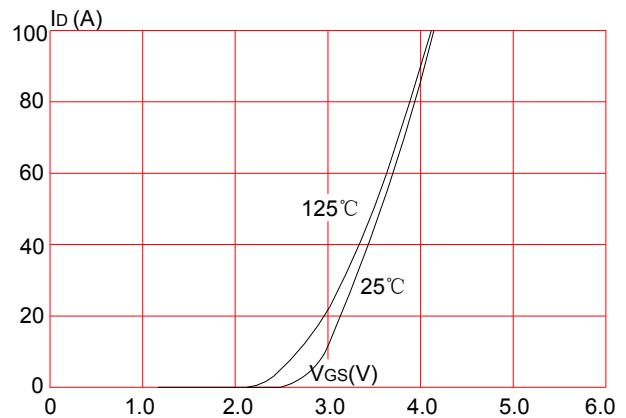
**Figure 3:** On-resistance vs. Drain Current



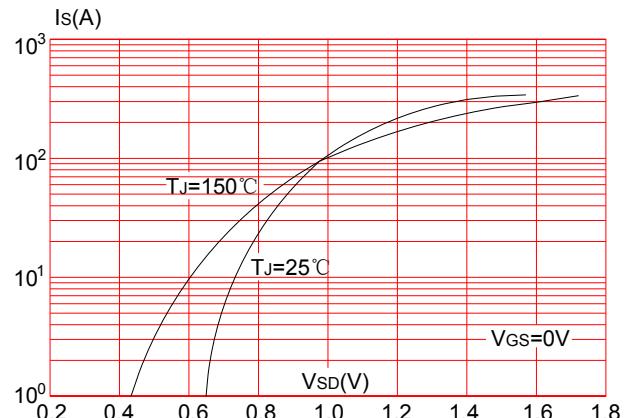
**Figure 5:** Gate Charge Characteristics



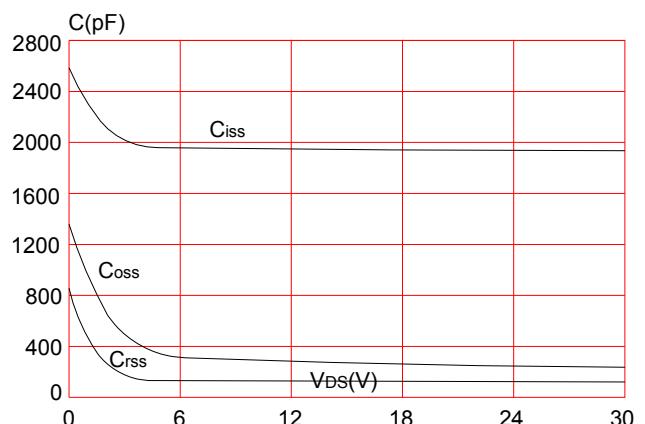
**Figure 2:** Typical Transfer Characteristics



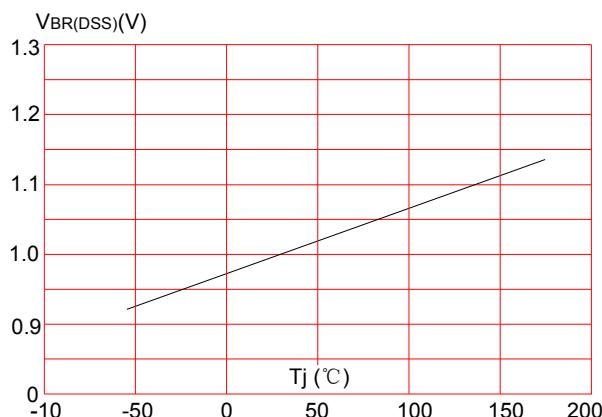
**Figure 4:** Body Diode Characteristics



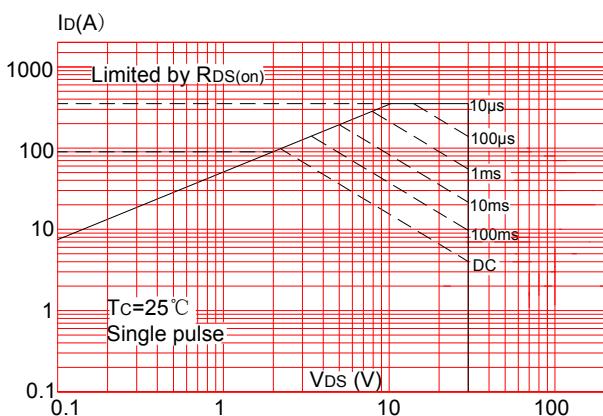
**Figure 6:** Capacitance Characteristics



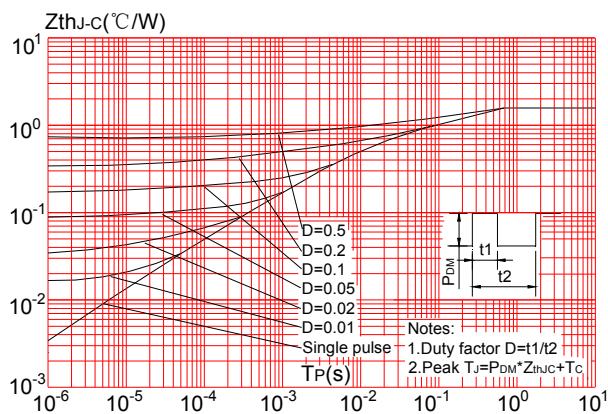
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



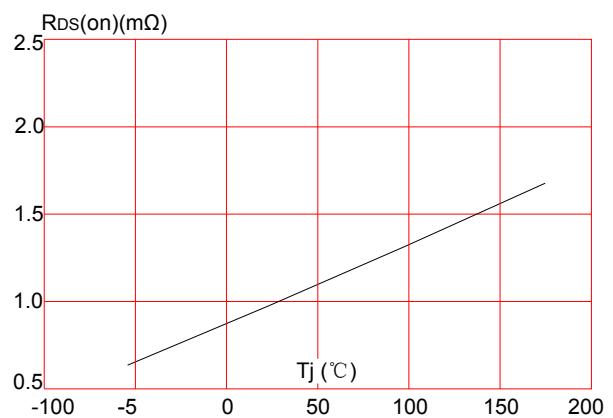
**Figure 9:** Maximum Safe Operating Area



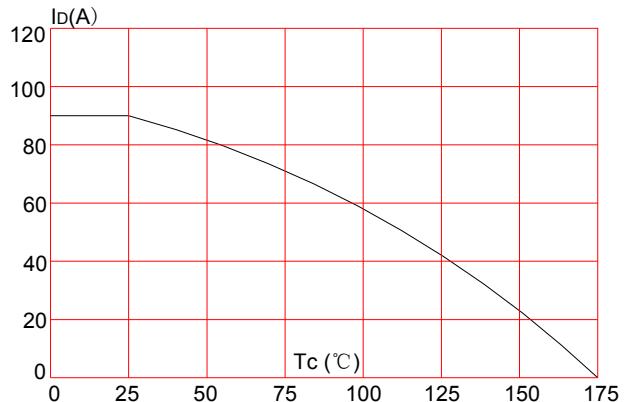
**Figure 11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-252)



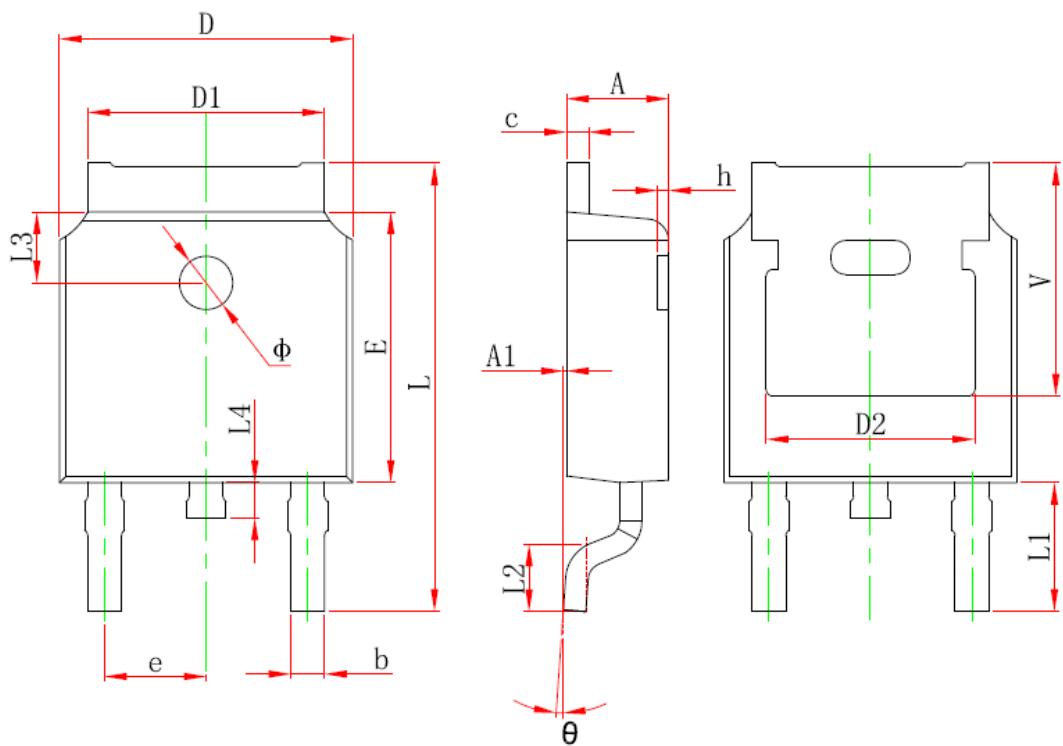
**Figure 8:** Normalized on Resistance vs. Junction Temperature



**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature



## TO-252-2L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
phi	1.100	1.300	0.043	0.051
theta	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	